

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N-CHANNEL DUAL GATE MOS TYPE

3SK293

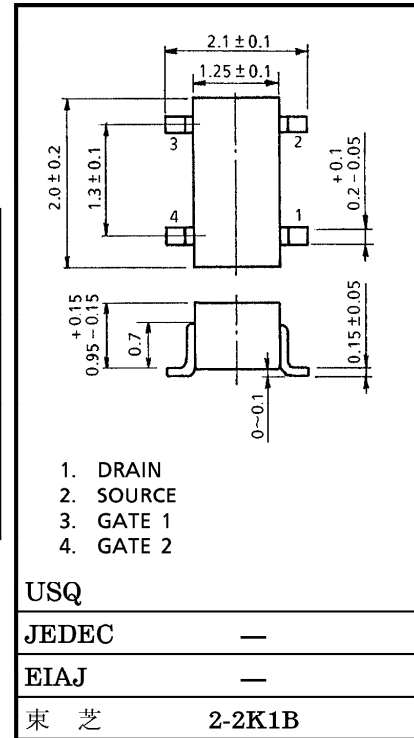
TV TUNER, UHF RF AMPLIFIER APPLICATIONS

単位 : mm

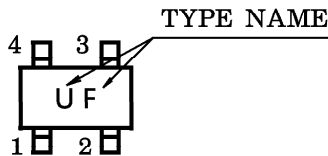
- Superior Cross Modulation Performance
- Low Reverse Transfer Capacitance : $C_{rss} = 16\text{fF}$ (Typ.)
- Low Noise Figure : $NF = 1.5\text{dB}$ (Typ.)

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DS}	12.5	V
Gate 1-Source Voltage	V_{G1S}	± 8	V
Gate 2-Source Voltage	V_{G2S}	± 8	V
Drain Current	I_D	30	mA
Drain Power Dissipation	P_D	100	mW
Channel Temperature	T_{ch}	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	$-55 \sim 125$	$^\circ\text{C}$



MARKING



Weight : 0.006g

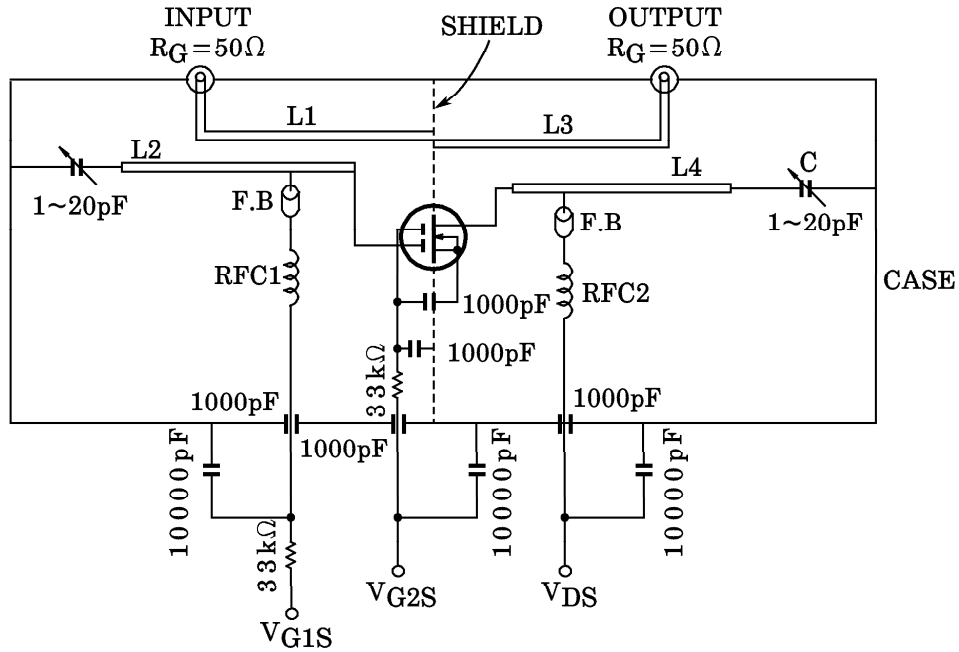
ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate 1 Leakage Current	I_{G1SS}	$V_{DS} = 0, V_{G1S} = \pm 6\text{V}, V_{G2S} = 0$	—	—	± 50	nA
Gate 2 Leakage Current	I_{G2SS}	$V_{DS} = 0, V_{G1S} = 0, V_{G2S} = \pm 6\text{V}$	—	—	± 50	nA
Drain-Source Voltage	$V_{(BR)DSX}$	$V_{G1S} = -0.5\text{V}, V_{G2S} = -0.5\text{V}, I_D = 100\mu\text{A}$	12.5	—	—	V
Drain Current	I_{DSS}	$V_{DS} = 6\text{V}, V_{G1S} = 0, V_{G2S} = 4.5\text{V}$	—	—	0.1	mA
Gate 1-Source Cut-off Voltage	$V_{G1S(OFF)}$	$V_{DS} = 6\text{V}, V_{G2S} = 4.5\text{V}, I_D = 100\mu\text{A}$	0.3	0.8	1.3	V
Gate 2-Source Cut-off Voltage	$V_{G2S(OFF)}$	$V_{DS} = 6\text{V}, V_{G1S} = 4.0\text{V}, I_D = 100\mu\text{A}$	0.5	1.0	1.5	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 6\text{V}, V_{G2S} = 4.5\text{V}, I_D = 10\text{mA}, f = 1\text{kHz}$	22	26	—	mS
Input Capacitance	C_{iss}	$V_{DS} = 6\text{V}, V_{G2S} = 4.5\text{V}, I_D = 10\text{mA}, f = 1\text{MHz}$	—	2.0	2.6	pF
Reverse Transfer Capacitance	C_{rss}		—	16	40	fF
Power Gain	G_{ps}	$V_{DS} = 6\text{V}, V_{G2S} = 4.5\text{V}, I_D = 10\text{mA}, f = 800\text{MHz}$	20	22.5	—	dB
Noise Figure	NF		—	1.5	2.5	dB

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Fig.1 800MHz G_{ps} , NF TEST CIRCUIT



- L1~L4 : ϕ 0.8mm SILVER PLATED COPPER WIRE
- C : AIR TRIMMER TTA25A200A (MURATA MFG, Co., Ltd.)
- RFC 1 : ϕ 0.35mm COPPER WIRE 3mm ID, 7T
- RFC 2 : ϕ 0.35mm COPPER WIRE 3mm ID, 10T

